

Contents

Foreword	V
Preface	VII
Resistively Detected ESR and ENDOR Experiments in Narrow and Wide Quantum Wells: A Comparative Study	
Joshua D. Caldwell, Clifford R. Bowers, Guennadii M. Gusev	1
1 Introduction	1
2 Theory	2
3 Experiment	4
4 Results	4
5 Conclusions	11
References	12
Index	13
Electron-Spin Manipulation in Quantum Dot Systems	
Yasuhiro Tokura, Toshiaki Obata, Tsuyoshi Hatano, Seigo Tarucha	15
1 Introduction	15
2 Single-Spin Manipulation	16
2.1 Oscillating Magnetic Field	17
2.2 Slanting Zeeman Field	19
3 Two-Spin Interaction	23
3.1 Formulation	23
3.2 Hybrid Double Dots	27
3.3 Double QD with Slanting Zeeman Field	30
4 Conclusion	31
References	31
Index	34
Resistively Detected NMR in GaAs/AlGaAs	
Guillaume Gervais	35
1 Nuclear Magnetic Resonances with 'Too Few Spins'	36

1.1	The ‘Too Few Spins’ Problem	36
1.2	Electrons as an In-Situ Detector of the NMR	37
2	Recent Advances in GaAs/AlGaAs Semiconductor Quantum Wells	40
2.1	Resistively Detected NMR Lineshapes in GaAs/AlGaAs	40
2.2	Spin-Lattice Relaxation-Time Measurements	43
3	Towards a Complete NMR Probe of Quantum Structures	46
3.1	NMR in Quantum Electronic Structures of GaAs/AlGaAs ...	46
3.2	NMR on a Chip: Quantum Coherent Control of the Nuclear Spins at the Nanoscale	47
4	Concluding Remarks	48
	References	48
	Index	49

Electron-Spin Dynamics in Self-Assembled (In,Ga)As/GaAs Quantum Dots

A. Greilich, D.R. Yakovlev, M. Bayer, A. Shabaev, Al.L. Efros	51
1 Introduction	51
2 Experiment	53
3 Electron g-Factor	54
4 Creation of Spin Coherence by Spin Initialization	56
5 Electron-Spin Coherence	65
6 Summary	77
References	78
Index	80

Single-Electron-Spin Measurements in Si-Based Semiconductor Nanostructures

H.W. Jiang, E. Yablonovitch, M. Xiao, M. Sakr, G. Scott, E.T. Croke .	81
1 Introduction	81
2 Measurements of a Single Spin in the SiO ₂ of a Submicrometer Si Field Effect Transistor	83
2.1 Statistical Measurements	84
2.2 Detection of Electron-Spin Resonance (ESR) of a Single Spin .	88
2.3 Single-Shot Measurement	91
3 Fabrication and Characterization of Electrostatically Confined Quantum-Dot Structures in Si/SiGe Heterostructures	91
3.1 Demonstration of a One-Electron Quantum Dot	92
3.2 Characterization of the Spin-Transition Sequence	95
3.3 Single-Shot Measurement	96
4 Concluding Remarks	98
References	98
Index	100

Si/SiGe Quantum Devices, Quantum Wells, and Electron-Spin Coherence

J.L. Truitt, K.A. Slinker, K.L.M. Lewis, D.E. Savage, Charles Tahan, L.J. Klein, J.O. Chu, P.M. Mooney, A.M. Tyryshkin, D.W. van der Weide, Robert Joynt, S.N. Coppersmith, Mark Friesen, M.A. Eriksson	101
1 Introduction	102
2 Silicon Quantum Devices	103
3 Spins and Valleys	106
4 ESR in Silicon Quantum Wells	107
5 Samples	109
6 ESR Measurements	110
7 Decoherence Analysis	111
8 Results	113
9 Conclusions	115
References	115
Index	126

Electrical Detection of Electron-Spin Resonance in Two-Dimensional Systems

Junya Matsunami, Tohru Okamoto	129
1 Mechanism of Electrical Detection	129
2 Determination of Spin-Relaxation Times	133
References	138
Index	140

Quantitative Treatment of Decoherence

Leonid Fedichkin, Vladimir Privman	141
1 Introduction	141
2 Measures of Decoherence	142
2.1 Relaxation Timescales	142
2.2 Quantum Entropy	143
2.3 Fidelity	143
2.4 Norm of Deviation	145
2.5 Arbitrary Initial States	145
3 Decoherence of Double Quantum-Dot Charge Qubits	146
3.1 Model	147
3.2 Piezoelectric Interaction	148
3.3 Deformation Interaction	150
3.4 Error Estimates During Gate Functions	151
3.5 Relaxation During the NOT Gate	151
3.6 Dephasing During a Phase Gate	154
3.7 Qubit Error Estimates	155

4	Additivity of Decoherence Measures	157
4.1	The Maximal Deviation Norm	158
4.2	Upper Bound for Measure of Decoherence	160
	References	162
	Index	167

Measuring the Charge and Spin States of Electrons on Individual Dopant Atoms in Silicon

Søren E.S. Andresen, Dane R. McCamey, Rolf Brenner, Marc A. Ahrens, Mladen Mitic, Victor C. Chan, Eric Gauja, Fay E. Hudson, Andrew J. Ferguson, Tilo M. Buehler, David J. Reilly, Robert G. Clark, Andrew S. Dzurak, Alex R. Hamilton, Cameron J. Wellard, Changyi Yang, Toby Hopf, Jeff McCallum, David N. Jamieson, Lloyd C. L. Hollenberg, Wayne D. Hutchison, Hans Huebl, Martin S. Brandt		169
1	Quantum Computing with Phosphorus in Silicon	170
1.1	Electronic Donor States of Phosphorus in Silicon	171
1.2	Coupled Pairs of Phosphorus Donors as Charge Qubits	171
2	Controlled Single-Ion Implantation	173
2.1	Single-Ion Detection with Integrated p-i-n Diodes	173
3	Charge Sensing with Superconducting RF-SETs	174
3.1	Layout and Performance of RF-SET Measurements	175
4	Initialization and Readout with Schottky Contacts	177
4.1	Contacting Atomically Doped Devices	177
5	Magnetic Resonance in Nanoscale Implanted Devices	178
	References	181
	Index	182

Electron Spin as a Spectrometer of Nuclear-Spin Noise and Other Fluctuations

Rogerio de Sousa		183
1	Introduction	183
2	Noise, Relaxation, and Decoherence	186
2.1	The Bloch–Wangsness–Redfield Master Equation	186
2.2	Finite Frequency Phase Fluctuations and Coherence Decay in the Semiclassical-Gaussian Approximation	188
2.3	Single-Spin Measurement Versus Ensemble Experiments: Different Coherence Times?	194
3	Electron-Spin Evolution Due to Nuclear Spins: Isotropic and Anisotropic Hyperfine Interactions, Internuclear Couplings and the Secular Approximation	196
3.1	The Electron–Nuclear Spin Hamiltonian	196

3.2	Electron–Nuclear-Spin Evolution in the Secular Approximation	198
3.3	Beyond the Secular Approximation: Nuclear–Nuclear Interactions Mediated by the Electron Spin Hyperfine Interaction	200
4	Microscopic Calculation of the Nuclear-Spin Noise Spectrum and Electron-Spin Decoherence	202
4.1	Nuclear-Spin Noise	203
4.2	Mean Field Theory of Noise Broadening: Quasiparticle Lifetimes	206
5	Electron Spin-Echo Decay of a Phosphorus Impurity in Silicon: Comparison with Experiment	209
5.1	Effective-Mass Model for a Phosphorus Impurity in Silicon ...	209
5.2	Explicit Calculations of the Nuclear-Spin Noise Spectrum and Electron Spin-Echo Decay of a Phosphorus Impurity in Silicon	210
6	Conclusions and Outlook for the Future	215
	References	218
	Index	220

A Robust and Fast Method to Compute Shallow States without Adjustable Parameters: Simulations for a Silicon-Based Qubit

	Alberto Debernardi, Marco Fanciulli	221
1	Shallow Impurities in an External Field	223
1.1	Envelope Function Approximation	224
1.2	The Central-Cell Correction	225
1.3	Numerical Basis Set	226
2	Phosphorous Impurity in Silicon	226
2.1	Bulk Ingredients	227
3	Theoretical Results: Si:P	227
3.1	The Core-Correction Contribution	228
3.2	Stark Effect	229
3.3	Electric-Field Dependence of Superhyperfine Constants	232
4	Confinement Effects	234
5	Conclusions	237
	References	238
	Index	239

Photon-Assisted Tunneling in Quantum Dots

	Enrico Prati, Rossella Latempa, Marco Fanciulli	241
1	Introduction	241
2	Theory of Photon-Assisted Tunneling in Quantum Dots	242

	Hamiltonian Formalism of Tunneling under Microwave Irradiation	243
	Tunneling in Quantum Dots under Microwave Irradiation	244
	Typical Regimes of Operation	246
3	Experimental Results in III–V Heterostructure Quantum Dots	247
4	Group IV Heterostructure Quantum Dots	250
5	Si/SiO ₂ nanoFET Quantum Dots	252
6	Conclusions	256
	References	257
	Index	258
	Index	259